

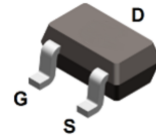
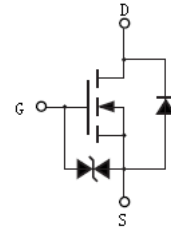


Features

- Fast switching speed
- HBM: JESD22-A114-B: 2
- RoHS compliant with Halogen-free

Mechanical Data

- Case: SOT-323
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208



SOT-323

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BSS138BKW	SOT-323	3000 pcs / Tape & Reel	138BK

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	60	V
Gate-to-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (T _A = 25°C) ^{*1}	I _D	450	mA
Continuous Drain Current (T _A = 70°C) ^{*1}		360	mA
Pulsed Drain Current (t _p = 10μs, T _A = 25°C)	I _{DM}	1800	mA
Power Dissipation (T _A = 25°C) ^{*1}	P _D	300	mW
Operating Junction Temperature Range	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Air ^{*1}	R _{θJA}	-	-	420	°C/W



Electrical Characteristics (@ T_A = 25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	60	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 60V, V _{GS} = 0V	-	-	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V, V _{DS} = 0V	-	-	±10	μA
On Characteristics						
R _{DS(ON)}	Static Drain-Source On-resistance ^{*2}	V _{GS} = 10V, I _D = 0.4A	-	0.56	0.7	Ω
		V _{GS} = 4.5V, I _D = 0.2A	-	0.64	1.2	
		V _{GS} = 2.5V, I _D = 0.1A	-	0.92	3	
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	0.8	1.0	1.5	V
R _G	Gate Resistance	V _{GS} = 0V, f = 1MHz	-	42	-	Ω
Dynamic Characteristics						
C _{ISS}	Input Capacitance	V _{GS} = 0V V _{DS} = 30V f = 1.0MHz	-	65	-	pF
C _{OSS}	Output Capacitance					
C _{RSS}	Reverse Transfer Capacitance					
Switching Characteristics						
t _{d(ON)}	Turn-on Delay Time ^{*3}	V _{DD} = 30V V _{GS} = 10V I _D = 0.36A R _G = 6Ω	-	2	-	ns
t _r	Turn-on Rise Time ^{*3}					
t _{d(OFF)}	Turn-Off Delay Time ^{*3}					
t _f	Turn-Off Fall Time ^{*3}					
Q _G	Total Gate-Charge	V _{DS} = 30V V _{GS} = 4.5V I _D = 0.2A	-	2.3	-	nC
Q _{GS}	Gate to Source Charge					
Q _{GD}	Gate to Drain (Miller) Charge					
Source-Drain Diode Characteristics						
V _{SD}	Diode Forward Voltage ^{*2}	I _S = 0.4A, V _{GS} = 0V	-	0.8	1.4	V

Notes:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper
2. The data tested by pulsed, pulse width ≤ 300μs, duty cycle ≤ 2%
3. Guaranteed by design, not subject to production



Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

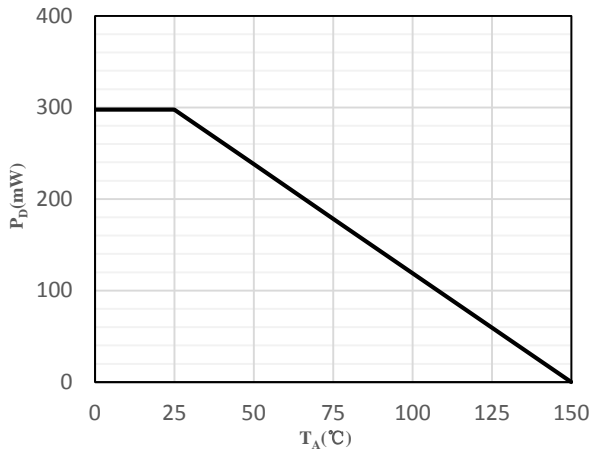


Fig 1 Power Dissipation

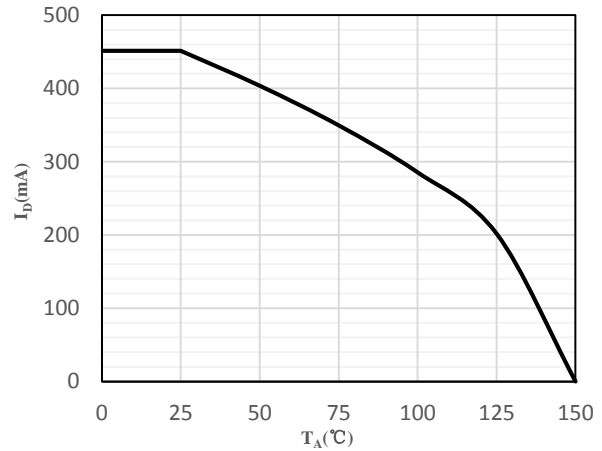


Fig 2 Drain Current

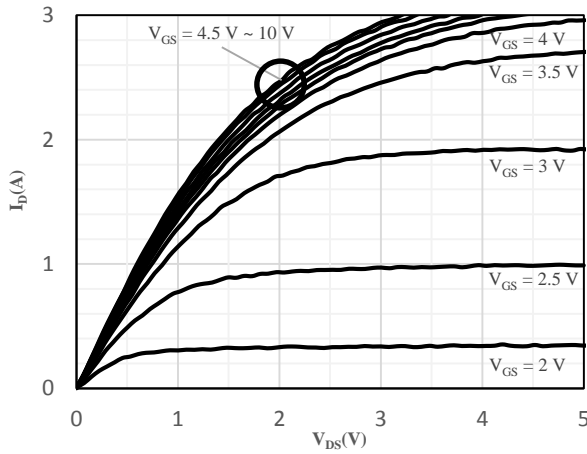


Fig 3 Typical Output Characteristics

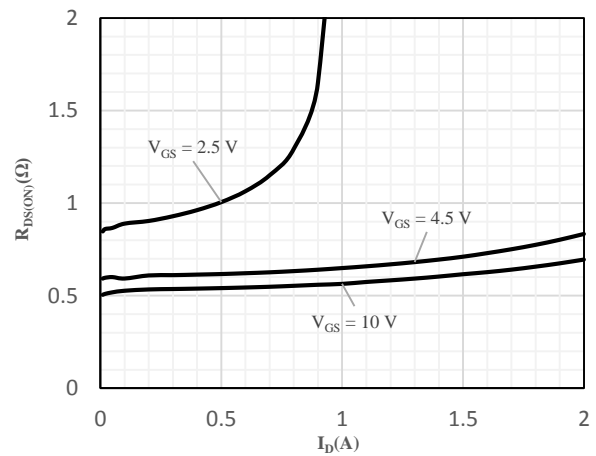


Fig 4 On-Resistance vs. Drain Current and Gate Voltage

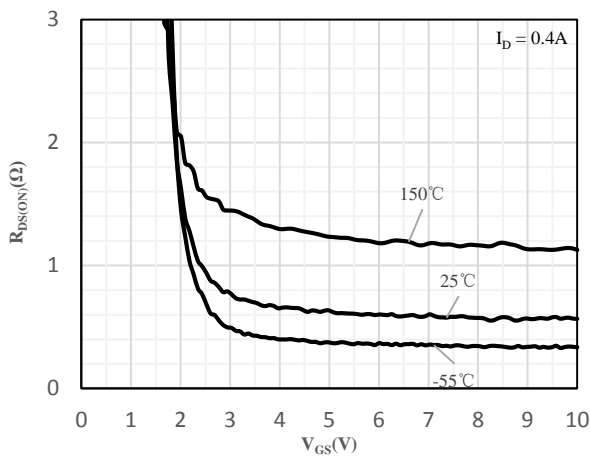


Fig 5 On-Resistance vs. Gate-Source Voltage

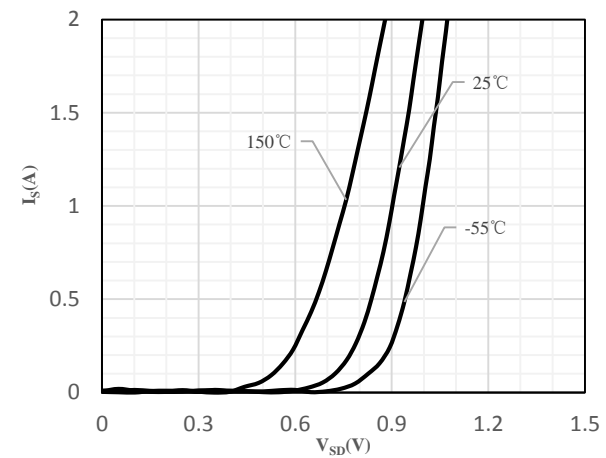


Fig 6 Body-Diode Characteristics

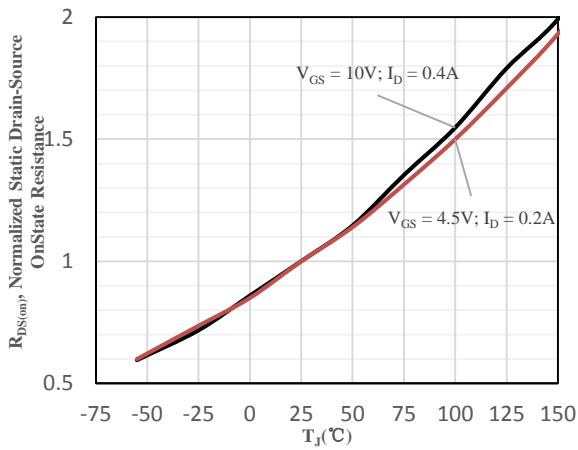


Fig 7 Normalized On-Resistance vs. Junction Temperature

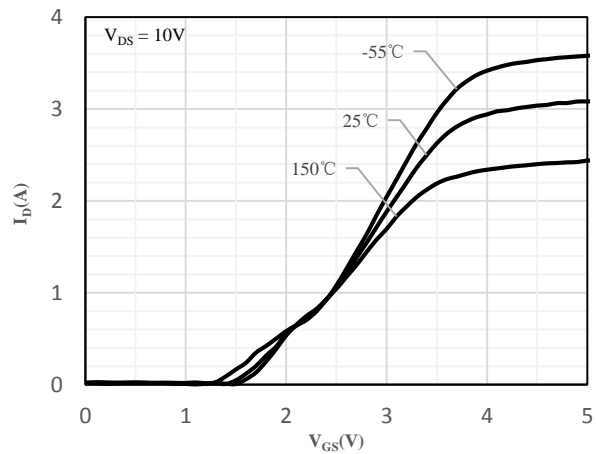


Fig 8 Transfer Characteristics

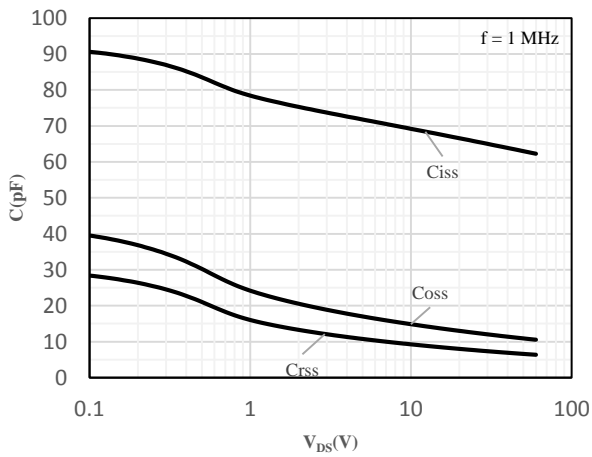


Fig 9 Capacitance Characteristics

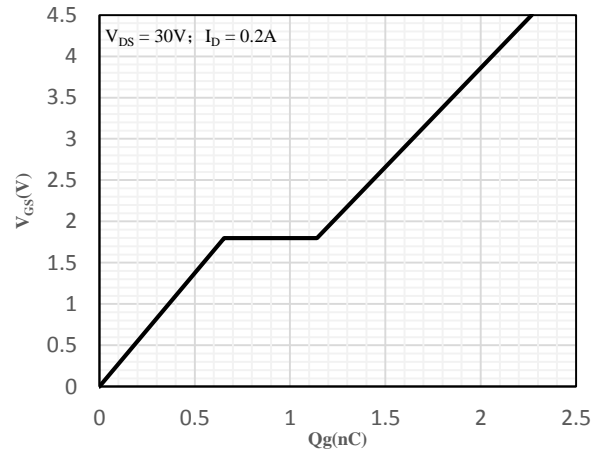


Fig 10 Gate-Charge Characteristics

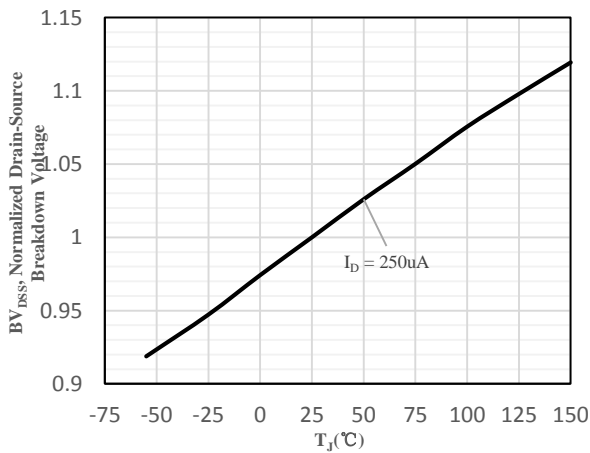


Fig 11 Normalized Breakdown Voltage vs. Junction Temperature

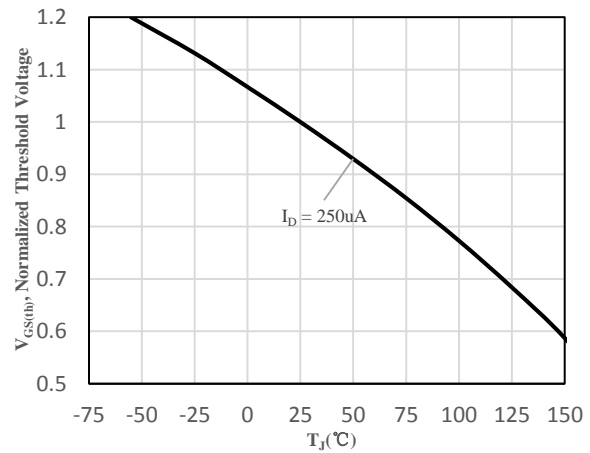
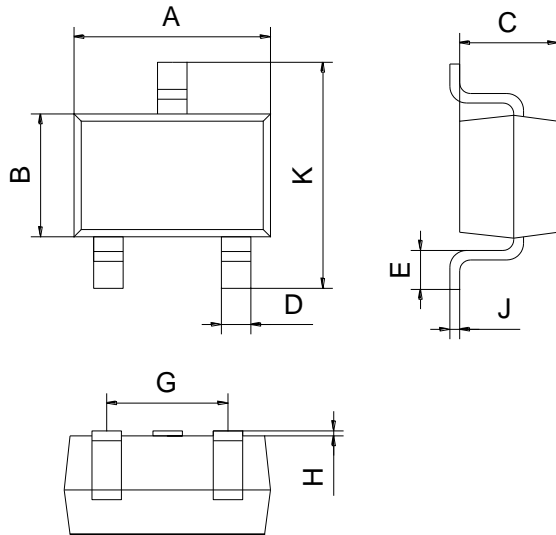


Fig 12 Normalized $V_{GS(th)}$ vs. Junction Temperature



Package Outline Dimensions (Unit: mm)



SOT-323		
Dimension	Min.	Max.
A	2.00	2.20
B	1.15	1.35
C	0.90	1.10
D	0.15	0.35
E	0.25	0.40
G	1.20	1.40
H	0.02	0.10
J	0.05	0.15
K	2.20	2.40

Mounting Pad Layout (Unit: mm)

SOT-323

